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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	189
Number of Gates	199000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50eqc240-2n

Functional Description

Each FLEX 10KE device contains an enhanced embedded array to implement memory and specialized logic functions, and a logic array to implement general logic.

The embedded array consists of a series of EABs. When implementing memory functions, each EAB provides 4,096 bits, which can be used to create RAM, ROM, dual-port RAM, or first-in first-out (FIFO) functions. When implementing logic, each EAB can contribute 100 to 600 gates towards complex logic functions, such as multipliers, microcontrollers, state machines, and DSP functions. EABs can be used independently, or multiple EABs can be combined to implement larger functions.

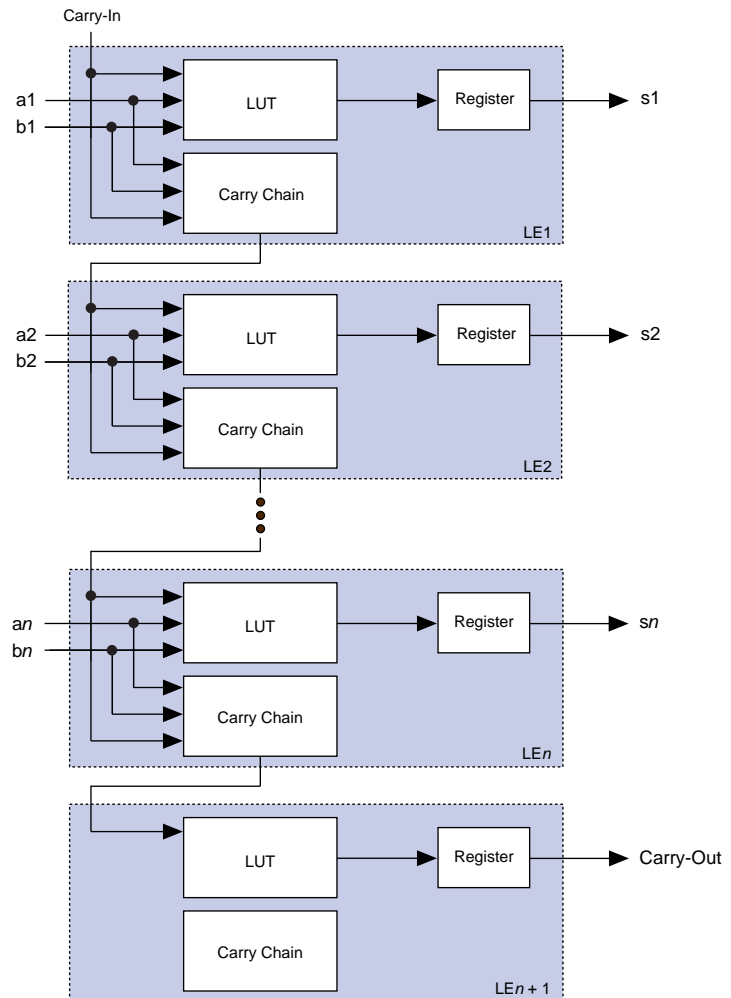
The logic array consists of logic array blocks (LABs). Each LAB contains eight LEs and a local interconnect. An LE consists of a four-input look-up table (LUT), a programmable flipflop, and dedicated signal paths for carry and cascade functions. The eight LEs can be used to create medium-sized blocks of logic—such as 8-bit counters, address decoders, or state machines—or combined across LABs to create larger logic blocks. Each LAB represents about 96 usable gates of logic.

Signal interconnections within FLEX 10KE devices (as well as to and from device pins) are provided by the FastTrack Interconnect routing structure, which is a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect routing structure. Each IOE contains a bidirectional I/O buffer and a flipflop that can be used as either an output or input register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. As inputs, they provide setup times as low as 0.9 ns and hold times of 0 ns. As outputs, these registers provide clock-to-output times as low as 3.0 ns. IOEs provide a variety of features, such as JTAG BST support, slew-rate control, tri-state buffers, and open-drain outputs.

Figure 9 shows how an n -bit full adder can be implemented in $n + 1$ LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for an accumulator function. Another portion of the LUT and the carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it can be used as a general-purpose signal.

Figure 9. FLEX 10KE Carry Chain Operation (n -Bit Full Adder)



FastTrack Interconnect Routing Structure

In the FLEX 10KE architecture, connections between LEs, EABs, and device I/O pins are provided by the FastTrack Interconnect routing structure, which is a series of continuous horizontal and vertical routing channels that traverses the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect routing structure consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the row. The column interconnect routes signals between rows and can drive I/O pins.

Row channels drive into the LAB or EAB local interconnect. The row signal is buffered at every LAB or EAB to reduce the effect of fan-out on delay. A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in a LAB drive the row interconnect.

Each column of LABs or EABs is served by a dedicated column interconnect. The column interconnect that serves the EABs has twice as many channels as other column interconnects. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs or EABs in the device. A signal from the column interconnect, which can be either the output of a LE or an input from an I/O pin, must be routed to the row interconnect before it can enter a LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, a LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This flexibility enables routing resources to be used more efficiently (see [Figure 13](#)).

Figure 13. FLEX 10KE LAB Connections to Row & Column Interconnect

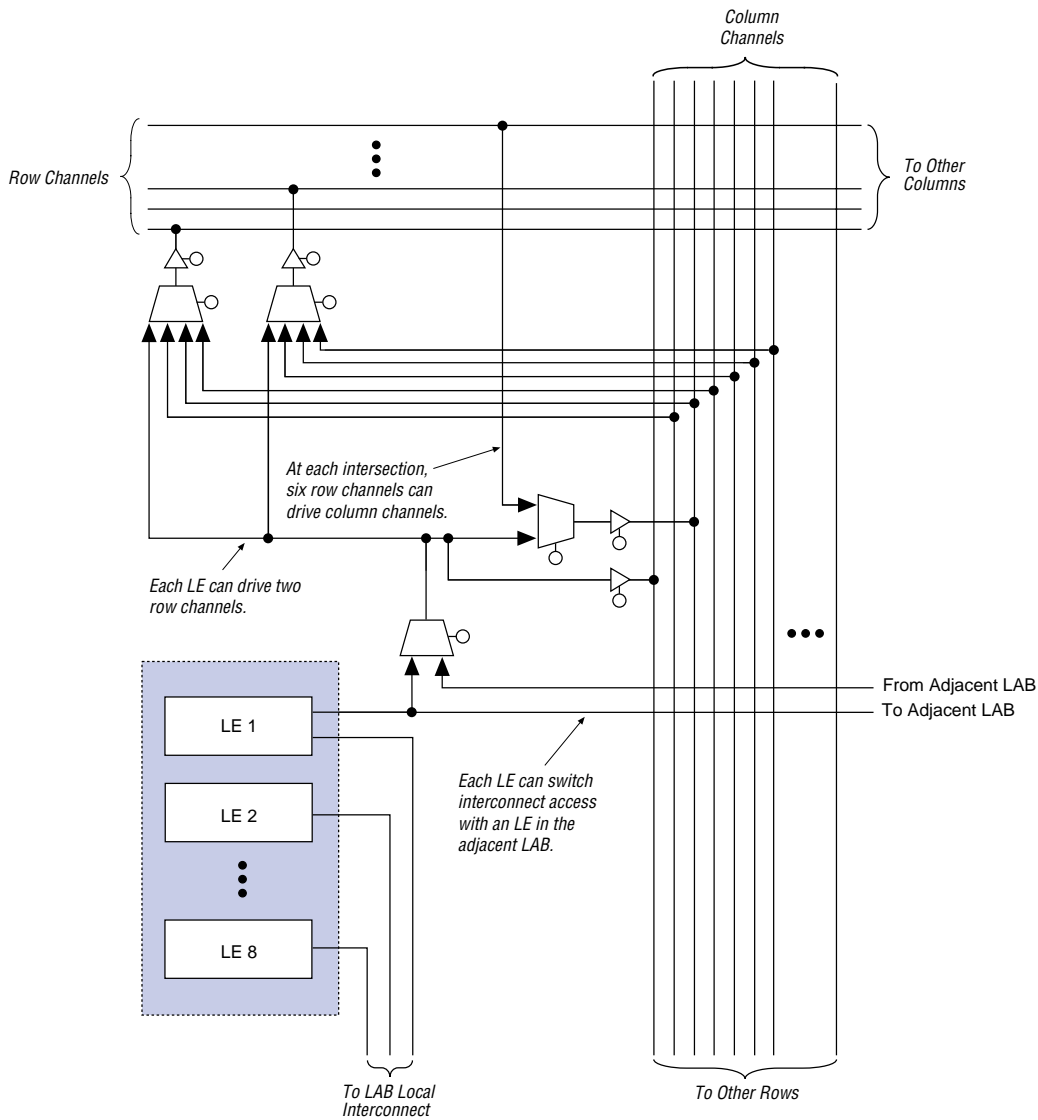
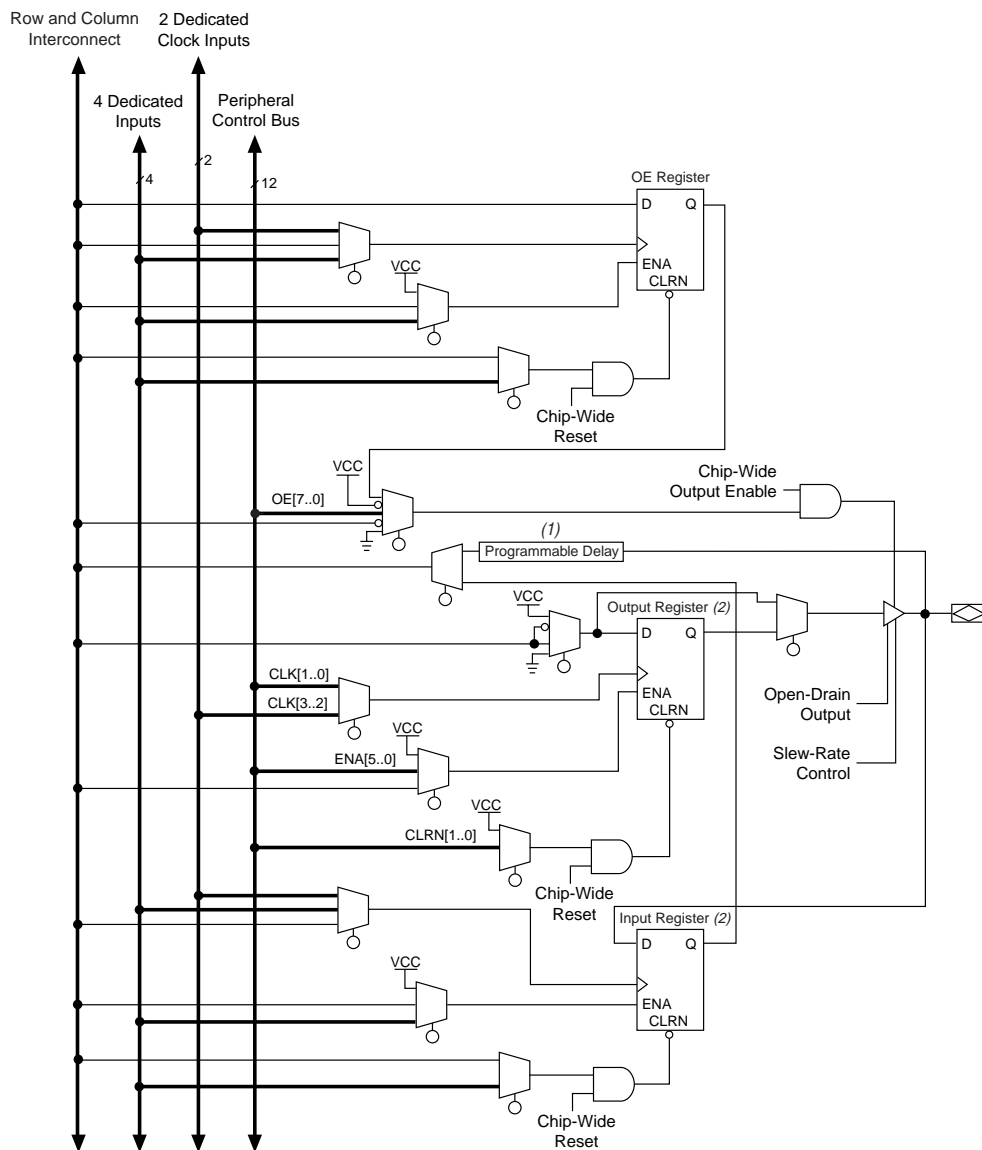


Figure 15. FLEX 10KE Bidirectional I/O Registers

**Note:**

- (1) All FLEX 10KE devices (except the EPF10K50E and EPF10K200E devices) have a programmable input delay buffer on the input path.

On all FLEX 10KE devices (except EPF10K50E and EPF10K200E devices), the input path from the I/O pad to the FastTrack Interconnect has a programmable delay element that can be used to guarantee a zero hold time. EPF10K50S and EPF10K200S devices also support this feature. Depending on the placement of the IOE relative to what it is driving, the designer may choose to turn on the programmable delay to ensure a zero hold time or turn it off to minimize setup time. This feature is used to reduce setup time for complex pin-to-register paths (e.g., PCI designs).

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across the device and provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, a LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal resets all IOE registers, overriding any other control signals.

When a dedicated clock pin drives IOE registers, it can be inverted for all IOEs in the device. All IOEs must use the same sense of the clock. For example, if any IOE uses the inverted clock, all IOEs must use the inverted clock and no IOE can use the non-inverted clock. However, LEs can still use the true or complement of the clock on a LAB-by-LAB basis.

The incoming signal may be inverted at the dedicated clock pin and will drive all IOEs. For the true and complement of a clock to be used to drive IOEs, drive it into both global clock pins. One global clock pin will supply the true, and the other will supply the complement.

When the true and complement of a dedicated input drives IOE clocks, two signals on the peripheral control bus are consumed, one for each sense of the clock.

Table 9. Peripheral Bus Sources for EPF10K100E, EPF10K130E, EPF10K200E & EPF10K200S Devices

Peripheral Control Signal	EPF10K100E	EPF10K130E	EPF10K200E EPF10K200S
OE0	Row A	Row C	Row G
OE1	Row C	Row E	Row I
OE2	Row E	Row G	Row K
OE3	Row L	Row N	Row R
OE4	Row I	Row K	Row O
OE5	Row K	Row M	Row Q
CLKENA0/CLK0/GLOBAL0	Row F	Row H	Row L
CLKENA1/OE6/GLOBAL1	Row D	Row F	Row J
CLKENA2/CLR0	Row B	Row D	Row H
CLKENA3/OE7/GLOBAL2	Row H	Row J	Row N
CLKENA4/CLR1	Row J	Row L	Row P
CLKENA5/CLK1/GLOBAL3	Row G	Row I	Row M

Signals on the peripheral control bus can also drive the four global signals, referred to as GLOBAL0 through GLOBAL3 in [Tables 8 and 9](#). An internally generated signal can drive a global signal, providing the same low-skew, low-delay characteristics as a signal driven by an input pin. An LE drives the global signal by driving a row line that drives the peripheral bus, which then drives the global signal. This feature is ideal for internally generated clear or clock signals with high fan-out. However, internally driven global signals offer no advantage over the general-purpose interconnect for routing data signals. The dedicated input pin should be driven to a known logic state (such as ground) and not be allowed to float.

The chip-wide output enable pin is an active-high pin (DEV_OE) that can be used to tri-state all pins on the device. This option can be set in the Altera software. On EPF10K50E and EPF10K200E devices, the built-in I/O pin pull-up resistors (which are active during configuration) are active when the chip-wide output enable pin is asserted. The registers in the IOE can also be reset by the chip-wide reset pin.

Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel (see Figure 16).

Figure 16. FLEX 10KE Row-to-IOE Connections

The values for m and n are provided in Table 10.

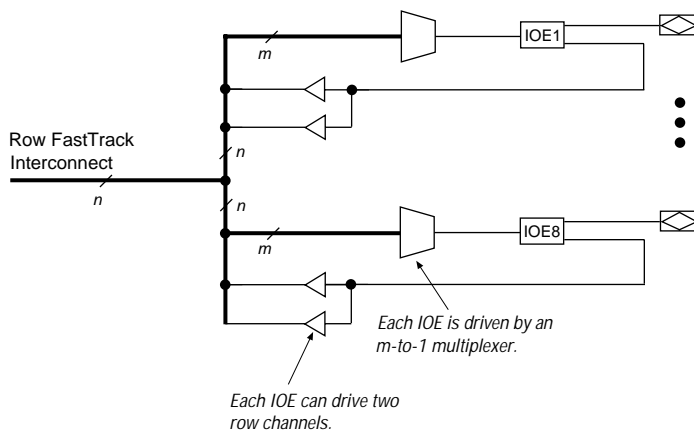


Table 10 lists the FLEX 10KE row-to-IOE interconnect resources.

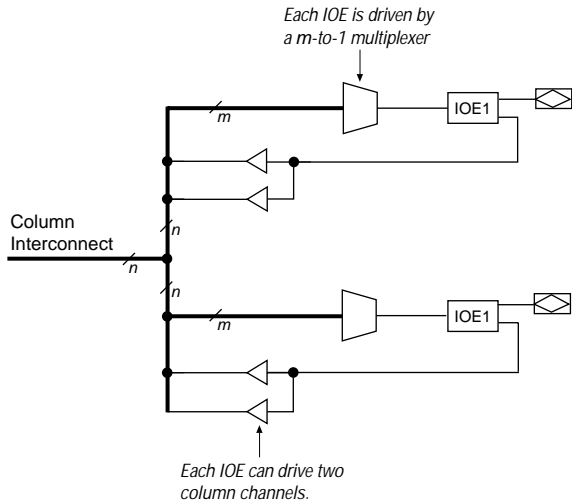
Table 10. FLEX 10KE Row-to-IOE Interconnect Resources		
Device	Channels per Row (n)	Row Channels per Pin (m)
EPF10K30E	216	27
EPF10K50E EPF10K50S	216	27
EPF10K100E	312	39
EPF10K130E	312	39
EPF10K200E EPF10K200S	312	39

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels is different for each IOE (see [Figure 17](#)).

Figure 17. FLEX 10KE Column-to-IOE Connections

The values for *m* and *n* are provided in [Table 11](#).



[Table 11](#) lists the FLEX 10KE column-to-IOE interconnect resources.

Table 11. FLEX 10KE Column-to-IOE Interconnect Resources		
Device	Channels per Column (<i>n</i>)	Column Channels per Pin (<i>m</i>)
EPF10K30E	24	16
EPF10K50E EPF10K50S	24	16
EPF10K100E	24	16
EPF10K130E	32	24
EPF10K200E EPF10K200S	48	40

Table 23. FLEX 10KE Device Capacitance *Note (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	$V_{IN} = 0\text{ V}$, $f = 1.0\text{ MHz}$		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	$V_{IN} = 0\text{ V}$, $f = 1.0\text{ MHz}$		12	pF
C_{OUT}	Output capacitance	$V_{OUT} = 0\text{ V}$, $f = 1.0\text{ MHz}$		10	pF

Notes to tables:

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Minimum DC input voltage is -0.5 V . During transitions, the inputs may undershoot to -2.0 V for input currents less than 100 mA and periods shorter than 20 ns .
- (3) Numbers in parentheses are for industrial-temperature-range devices.
- (4) Maximum V_{CC} rise time is 100 ms , and V_{CC} must rise monotonically.
- (5) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (6) Typical values are for $T_A = 25^\circ\text{ C}$, $V_{CCINT} = 2.5\text{ V}$, and $V_{CCIO} = 2.5\text{ V}$ or 3.3 V .
- (7) These values are specified under the FLEX 10KE Recommended Operating Conditions shown in [Tables 20 and 21](#).
- (8) The FLEX 10KE input buffers are compatible with 2.5-V , 3.3-V (LVTTTL and LVCMOS), and 5.0-V TTL and CMOS signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in [Figure 22](#).
- (9) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
- (10) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
- (11) This value is specified for normal device operation. The value may vary during power-up.
- (12) This parameter applies to -1 speed-grade commercial-temperature devices and -2 speed-grade-industrial temperature devices.
- (13) Pin pull-up resistance values will be lower if the pin is driven higher than V_{CCIO} by an external source.
- (14) Capacitance is sample-tested only.

Figure 22 shows the required relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance.

Figure 22. Relationship between V_{CCIO} & V_{CCINT} for 3.3-V PCI Compliance

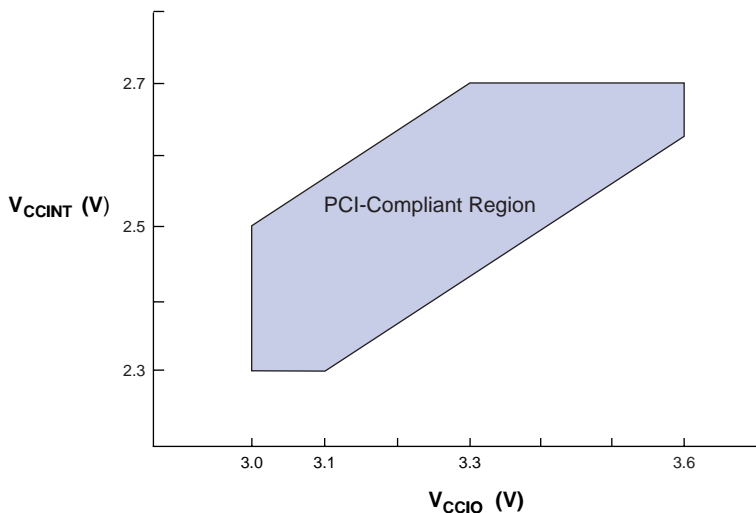


Figure 23 shows the typical output drive characteristics of FLEX 10KE devices with 3.3-V and 2.5-V V_{CCIO} . The output driver is compliant to the 3.3-V **PCI Local Bus Specification, Revision 2.2** (when V_{CCIO} pins are connected to 3.3 V). FLEX 10KE devices with a -1 speed grade also comply with the drive strength requirements of the **PCI Local Bus Specification, Revision 2.2** (when V_{CCINT} pins are powered with a minimum supply of 2.375 V, and V_{CCIO} pins are connected to 3.3 V). Therefore, these devices can be used in open 5.0-V PCI systems.

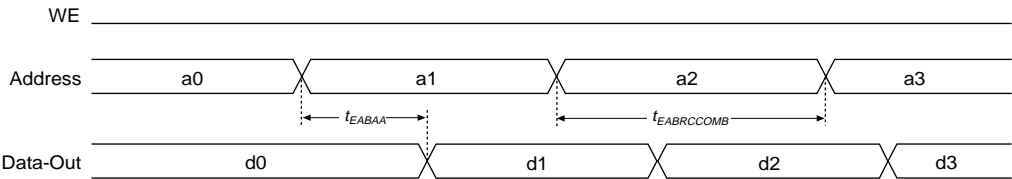
Table 26. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABRE1}	Read enable delay to EAB for combinatorial input	
t_{EABRE2}	Read enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{EABCLR}	EAB register asynchronous clear time to output delay	
t_{AA}	Address access delay (including the read enable to output delay)	
t_{WP}	Write pulse width	
t_{RP}	Read pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	(5)
t_{WDH}	Data hold time after falling edge of write pulse	(5)
t_{WASU}	Address setup time before rising edge of write pulse	(5)
t_{WAH}	Address hold time after falling edge of write pulse	(5)
t_{RASU}	Address setup time with respect to the falling edge of the read enable	
t_{RAH}	Address hold time with respect to the falling edge of the read enable	
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, or the EAB macroparameters in Tables 26 and 27.

Figure 29. EAB Asynchronous Timing Waveforms

EAB Asynchronous Read



EAB Asynchronous Write

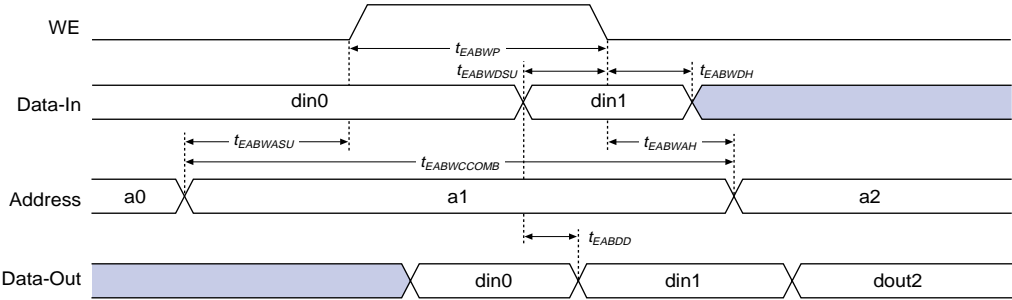


Table 31. EPF10K30E Device LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CGENR}		0.1		0.1		0.2	ns
t_{CASC}		0.6		0.8		1.0	ns
t_C		0.0		0.0		0.0	ns
t_{CO}		0.3		0.4		0.5	ns
t_{COMB}		0.4		0.4		0.6	ns
t_{SU}	0.4		0.6		0.6		ns
t_H	0.7		1.0		1.3		ns
t_{PRE}		0.8		0.9		1.2	ns
t_{CLR}		0.8		0.9		1.2	ns
t_{CH}	2.0		2.5		2.5		ns
t_{CL}	2.0		2.5		2.5		ns

Table 32. EPF10K30E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.4		2.8		3.8	ns
t_{IOC}		0.3		0.4		0.5	ns
t_{IOCO}		1.0		1.1		1.6	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	1.2		1.4		1.9		ns
t_{IOH}	0.3		0.4		0.5		ns
t_{IOCLR}		1.0		1.1		1.6	ns
t_{OD1}		1.9		2.3		3.0	ns
t_{OD2}		1.4		1.8		2.5	ns
t_{OD3}		4.4		5.2		7.0	ns
t_{XZ}		2.7		3.1		4.3	ns
t_{ZX1}		2.7		3.1		4.3	ns
t_{ZX2}		2.2		2.6		3.8	ns
t_{ZX3}		5.2		6.0		8.3	ns
t_{INREG}		3.4		4.1		5.5	ns
t_{IOFD}		0.8		1.3		2.4	ns
t_{INCOMB}		0.8		1.3		2.4	ns

Table 47. EPF10K100E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		2.0		2.6	ns
$t_{EABDATA1}$		0.0		0.0		0.0	ns
t_{EABWE1}		1.5		2.0		2.6	ns
t_{EABWE2}		0.3		0.4		0.5	ns
t_{EABRE1}		0.3		0.4		0.5	ns
t_{EABRE2}		0.0		0.0		0.0	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.4		0.5	ns
$t_{EABYPASS}$		0.1		0.1		0.2	ns
t_{EABSU}	0.8		1.0		1.4		ns
t_{EABH}	0.1		0.1		0.2		ns
t_{EABCLR}	0.3		0.4		0.5		ns
t_{AA}		4.0		5.1		6.6	ns
t_{WP}	2.7		3.5		4.7		ns
t_{RP}	1.0		1.3		1.7		ns
t_{WDSU}	1.0		1.3		1.7		ns
t_{WDH}	0.2		0.2		0.3		ns
t_{WASU}	1.6		2.1		2.8		ns
t_{WAH}	1.6		2.1		2.8		ns
t_{RASU}	3.0		3.9		5.2		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		1.5		2.0		2.6	ns
t_{DD}		1.5		2.0		2.6	ns
t_{EABOUT}		0.2		0.3		0.3	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	2.7		3.5		4.7		ns

Table 48. EPF10K100E Device EAB Internal Timing Macroparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		5.9		7.6		9.9	ns
$t_{EABRCOMB}$	5.9		7.6		9.9		ns
$t_{EABRCREG}$	5.1		6.5		8.5		ns
t_{EABWP}	2.7		3.5		4.7		ns

Table 48. EPF10K100E Device EAB Internal Timing Macroparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABWCOMB}$	5.9		7.7		10.3		ns
$t_{EABWCREG}$	5.4		7.0		9.4		ns
t_{EABDD}		3.4		4.5		5.9	ns
$t_{EABDATACO}$		0.5		0.7		0.8	ns
$t_{EABDATASU}$	0.8		1.0		1.4		ns
$t_{EABDATAH}$	0.1		0.1		0.2		ns
$t_{EABWESU}$	1.1		1.4		1.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.0		1.3		1.7		ns
t_{EABWDH}	0.2		0.2		0.3		ns
$t_{EABWASU}$	4.1		5.2		6.8		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		3.4		4.5		5.9	ns

Table 49. EPF10K100E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.6		4.4	ns
t_{DIN2LE}		0.3		0.4		0.5	ns
$t_{DIN2DATA}$		1.6		1.8		2.0	ns
$t_{DCLK2IOE}$		0.8		1.1		1.4	ns
$t_{DCLK2LE}$		0.3		0.4		0.5	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		2.5		3.4	ns
$t_{SAMECOLUMN}$		0.4		1.0		1.6	ns
$t_{DIFFROW}$		1.9		3.5		5.0	ns
$t_{TROWROWS}$		3.4		6.0		8.4	ns
$t_{LEPERIPH}$		4.3		5.4		6.5	ns
$t_{LABCARRY}$		0.5		0.7		0.9	ns
$t_{LABCASC}$		0.8		1.0		1.4	ns

Table 50. EPF10K100E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
$t_{\text{INSU}}^{(3)}$	2.0		2.5		3.3		ns
$t_{\text{INH}}^{(3)}$	0.0		0.0		0.0		ns
$t_{\text{OUTCO}}^{(3)}$	2.0	5.2	2.0	6.9	2.0	9.1	ns
$t_{\text{INSU}}^{(4)}$	2.0		2.2		—		ns
$t_{\text{INH}}^{(4)}$	0.0		0.0		—		ns
$t_{\text{OUTCO}}^{(4)}$	0.5	3.0	0.5	4.6	—	—	ns
t_{PCISU}	3.0		6.2		—		ns
t_{PCIH}	0.0		0.0		—		ns
t_{PCICO}	2.0	6.0	2.0	6.9	—	—	ns

Table 51. EPF10K100E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}^{(3)}$	1.7		2.5		3.3		ns
$t_{\text{INHBIDIR}}^{(3)}$	0.0		0.0		0.0		ns
$t_{\text{INSUBIDIR}}^{(4)}$	2.0		2.8		—		ns
$t_{\text{INHBIDIR}}^{(4)}$	0.0		0.0		—		ns
$t_{\text{OUTCOBIDIR}}^{(3)}$	2.0	5.2	2.0	6.9	2.0	9.1	ns
$t_{\text{XZBIDIR}}^{(3)}$		5.6		7.5		10.1	ns
$t_{\text{ZXBIDIR}}^{(3)}$		5.6		7.5		10.1	ns
$t_{\text{OUTCOBIDIR}}^{(4)}$	0.5	3.0	0.5	4.6	—	—	ns
$t_{\text{XZBIDIR}}^{(4)}$		4.6		6.5		—	ns
$t_{\text{ZXBIDIR}}^{(4)}$		4.6		6.5		—	ns

Notes to tables:

- (1) All timing parameters are described in Tables 24 through 30 in this data sheet.
- (2) These parameters are specified by characterization.
- (3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
- (4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Table 64. EPF10K200E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		10.0		12.0		16.0	ns
t_{INSU}	2.8		3.4		4.4		ns
t_{INH}	0.0		0.0		0.0		ns
t_{OUTCO}	2.0	4.5	2.0	5.3	2.0	7.8	ns
t_{PCISU}	3.0		6.2		-		ns
t_{PCIH}	0.0		0.0		-		ns
t_{PCICO}	2.0	6.0	2.0	8.9	-	-	ns

Table 65. EPF10K200E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	3.0		4.0		5.5		ns
t_{INHBIDIR}	0.0		0.0		0.0		ns
$t_{\text{OUTCOBIDIR}}$	2.0	4.5	2.0	5.3	2.0	7.8	ns
t_{XZBIDIR}		8.1		9.5		13.0	ns
t_{ZXBIDIR}		8.1		9.5		13.0	ns

Notes to tables:

- (1) All timing parameters are described in [Tables 24](#) through [30](#) in this data sheet.
 (2) These parameters are specified by characterization.

[Tables 66](#) through [79](#) show EPF10K50S and EPF10K200S device external timing parameters.

Table 66. EPF10K50S Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.8		1.1	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.6		0.7		0.9	ns
t_{PACKED}		0.2		0.3		0.4	ns
t_{EN}		0.6		0.7		0.9	ns
t_{CICO}		0.1		0.1		0.1	ns
t_{CGEN}		0.4		0.5		0.6	ns

Table 71. EPF10K50S External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		8.0		9.5		12.5	ns
$t_{\text{INSU}}^{(2)}$	2.4		2.9		3.9		ns
$t_{\text{INH}}^{(2)}$	0.0		0.0		0.0		ns
$t_{\text{OUTCO}}^{(2)}$	2.0	4.3	2.0	5.2	2.0	7.3	ns
$t_{\text{INSU}}^{(3)}$	2.4		2.9				ns
$t_{\text{INH}}^{(3)}$	0.0		0.0				ns
$t_{\text{OUTCO}}^{(3)}$	0.5	3.3	0.5	4.1			ns
t_{PCISU}	2.4		2.9		—		ns
t_{PCIH}	0.0		0.0		—		ns
t_{PCICO}	2.0	6.0	2.0	7.7	—	—	ns

Table 72. EPF10K50S External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}^{(2)}$	2.7		3.2		4.3		ns
$t_{\text{INHBIDIR}}^{(2)}$	0.0		0.0		0.0		ns
$t_{\text{INHBIDIR}}^{(3)}$	0.0		0.0		—		ns
$t_{\text{INSUBIDIR}}^{(3)}$	3.7		4.2		—		ns
$t_{\text{OUTCOBIDIR}}^{(2)}$	2.0	4.5	2.0	5.2	2.0	7.3	ns
$t_{\text{XZBIDIR}}^{(2)}$		6.8		7.8		10.1	ns
$t_{\text{ZXBIDIR}}^{(2)}$		6.8		7.8		10.1	ns
$t_{\text{OUTCOBIDIR}}^{(3)}$	0.5	3.5	0.5	4.2	—	—	
$t_{\text{XZBIDIR}}^{(3)}$		6.8		8.4		—	ns
$t_{\text{ZXBIDIR}}^{(3)}$		6.8		8.4		—	ns

Notes to tables:

- (1) All timing parameters are described in [Tables 24 through 30](#).
- (2) This parameter is measured without use of the ClockLock or ClockBoost circuits.
- (3) This parameter is measured with use of the ClockLock or ClockBoost circuits

Table 74. EPF10K200S Device IOE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ZX2}		4.5		4.8		6.6	ns
t_{ZX3}		6.6		7.6		10.1	ns
t_{INREG}		3.7		5.7		7.7	ns
t_{IOFD}		1.8		3.4		4.0	ns
t_{INCOMB}		1.8		3.4		4.0	ns

Table 75. EPF10K200S Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.8		2.4		3.2	ns
$t_{EABDATA1}$		0.4		0.5		0.6	ns
t_{EABWE1}		1.1		1.7		2.3	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0		0		0	ns
t_{EABRE2}		0.4		0.5		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		0.9		1.2	ns
$t_{EABYPASS}$		0.0		0.1		0.1	ns
t_{EABSU}	0.7		1.1		1.5		ns
t_{EABH}	0.4		0.5		0.6		ns
t_{EABCLR}	0.8		0.9		1.2		ns
t_{AA}		2.1		3.7		4.9	ns
t_{WP}	2.1		4.0		5.3		ns
t_{RP}	1.1		1.1		1.5		ns
t_{WDSU}	0.5		1.1		1.5		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.1		1.6		2.1		ns
t_{WAH}	1.6		2.5		3.3		ns
t_{RASU}	1.6		2.6		3.5		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		2.0		2.4		3.2	ns
t_{DD}		2.0		2.4		3.2	ns
t_{EABOUT}		0.0		0.1		0.1	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	2.1		2.8		3.8		ns